

Abstracts

Ka-band ultra low noise MMIC amplifier using pseudomorphic HEMTs (1997 [RFIC])

S. Fujimoto, T. Katoh, T. Ishida, T. Oku, Y. Sasaki, T. Ishikawa and Y. Mitsui. "Ka-band ultra low noise MMIC amplifier using pseudomorphic HEMTs (1997 [RFIC])." 1997 Radio Frequency Integrated Circuits (RFIC) Symposium 97. (1997 [RFIC]): 169-172.

A Ka-band monolithic low noise two stage amplifier has been developed using an AlGaAs-InGaAs-GaAs pseudomorphic HEMTs with a gate length of 0.15 μm . For a superior noise figure, the MMIC was optimized by inserting a low loss resonator type stabilizing circuit without sacrificing the gain performance. The amplifier has achieved a 1.0 dB noise figure with an associated gain of 18.0 dB at 32 GHz. These results are the best of AlGaAs-InGaAs-GaAs P-HEMT MMICs ever reported to date.

 [Return to main document.](#)